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Modelling Low Charge Ions in the Solar Atmosphere

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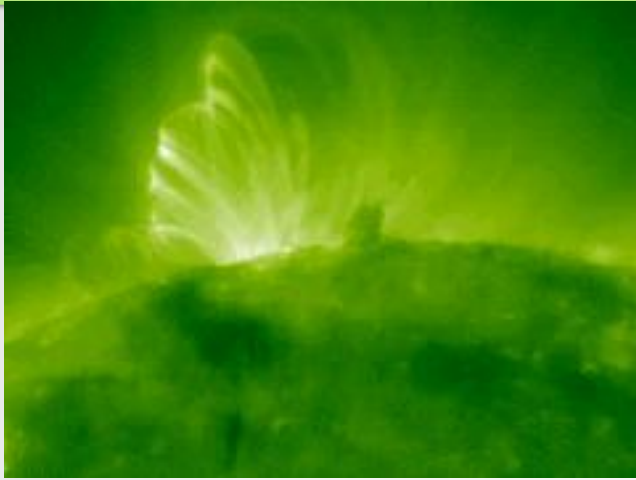
Pete Storey

(University College London)

MNRAS 2020, 497, 1443; MNRAS 2021a, 503, 1976; MNRAS 2021b, 505, 3968

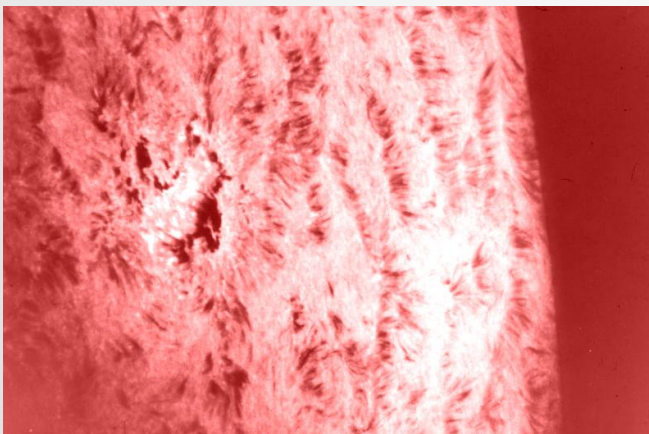
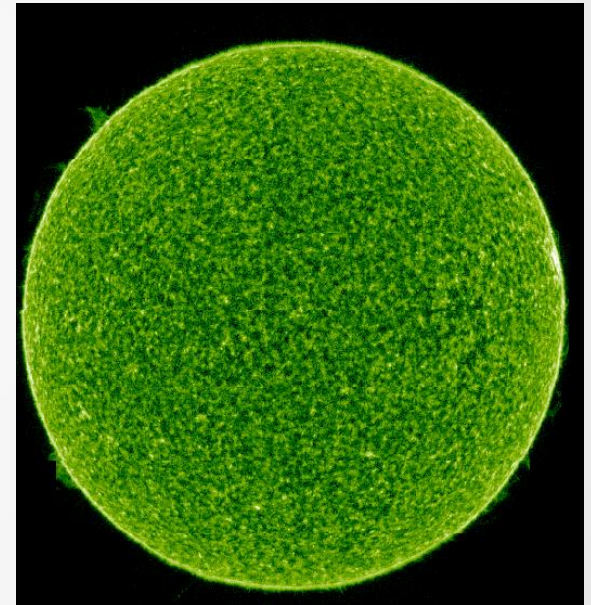


Background



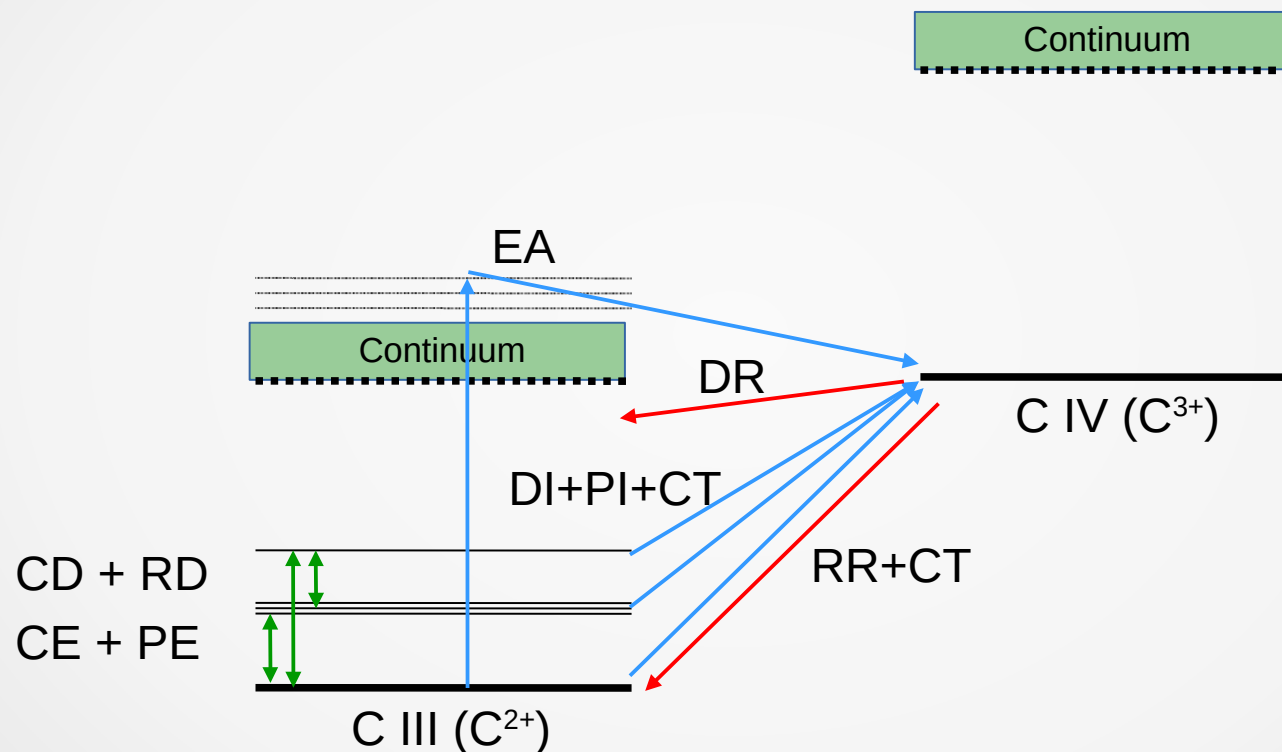
Corona (6×10^5 - 3×10^6 K) – steady state equilibrium, independent atom models, ground level ionisation and recombination

Transition region (25000- 6×10^5 K) -
?



Chromosphere (6000-25000K)– Time-dependent ionisation, radiation hydrodynamics, photo-induced processes, charge transfer, inelastic collisions with hydrogen.

Modelling: Level Resolved



DI – Direct Ionisation

PI – Photo-ionisation

EA – Excitation-Autoionisation

RR/RD – Radiative Recombination/Decay

DR – Dielectronic Recombination

CT – Charge Transfer

CE/CD – Collisional Excitation/De-excitation

PE – Photo-excitation

Methods: Modelling new atomic processes

Density effects

Ionisation and recombination from metastable levels:

New ionisation rate calculations for carbon and oxygen, using Flexible Atomic Code (Gu, 2008, Can. J. Phys., 86, 675) and Autostructure (Badnell 2011, CPC, 182, 1528)

Recombination data from APAP Network (Badnell 2006, ApJS, 167, 334, Badnell et al, 2003, A&A, 406, 1151)

Suppression of dielectronic recombination:

Estimated from data of Summers, 1974, MNRAS, 169, 663.

Photo-ionisation

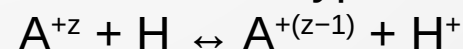
$$\alpha_{ij}^{PI} = 4\pi \int_{\nu_0}^{\infty} \frac{\sigma_{ij}(\nu)}{h\nu} J_{\nu} d\nu$$

Cross sections from Badnell N. R., 2006, ApJS, 167, 334.

Radiances from Woods T. N., et al., 2009, Geophys. Res. Lett., 36, L01101.

Charge transfer

Reactions of type:

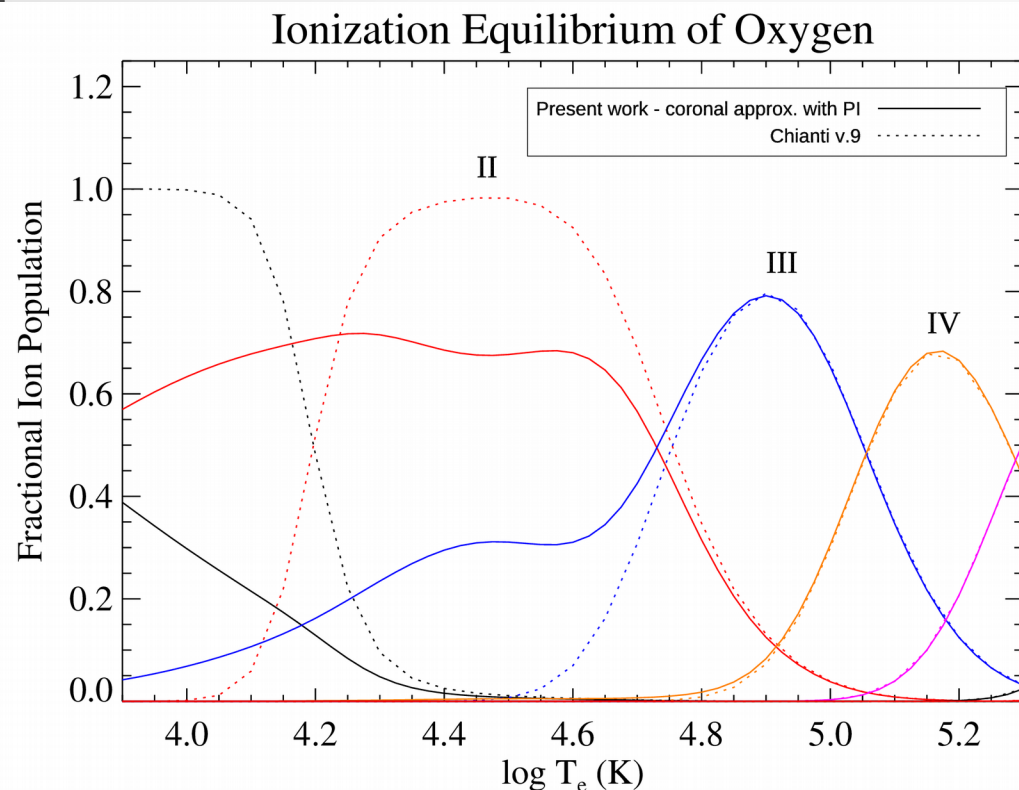


$$R_{CT}(T_e) = \frac{N_{HI}}{N_H} \frac{N_H}{N_e} N_e \alpha_{CT}(T_e)$$

Hydrogen fractional populations taken from Avrett E. H., Loeser R., 2008, ApJS, 175, 229

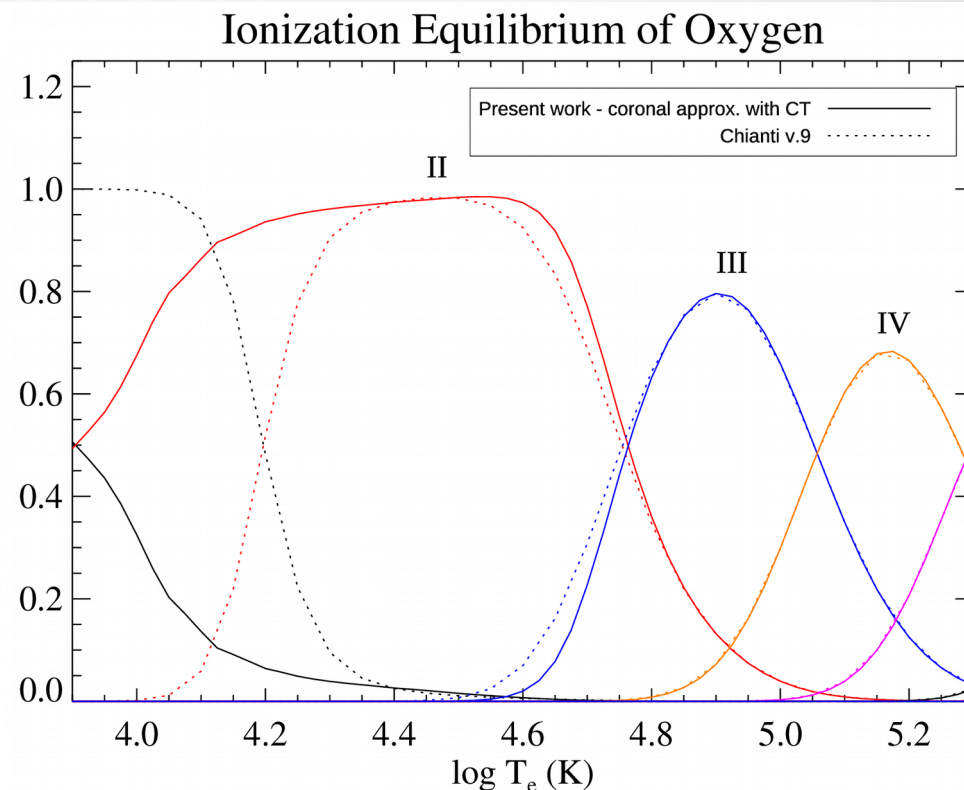
Results: Ion Populations

With photo-ionisation only



- O I depleted by both processes
- O II enhanced at low temperature
- Charge transfer opposes photo-ionisation of O II at higher temperature

With charge transfer only



Charge transfer data:

Stancil P. C., et al. 1999A, J. Phys. B, 32, 1523

Barragán P., et al. 2006, ApJ, 636, 544

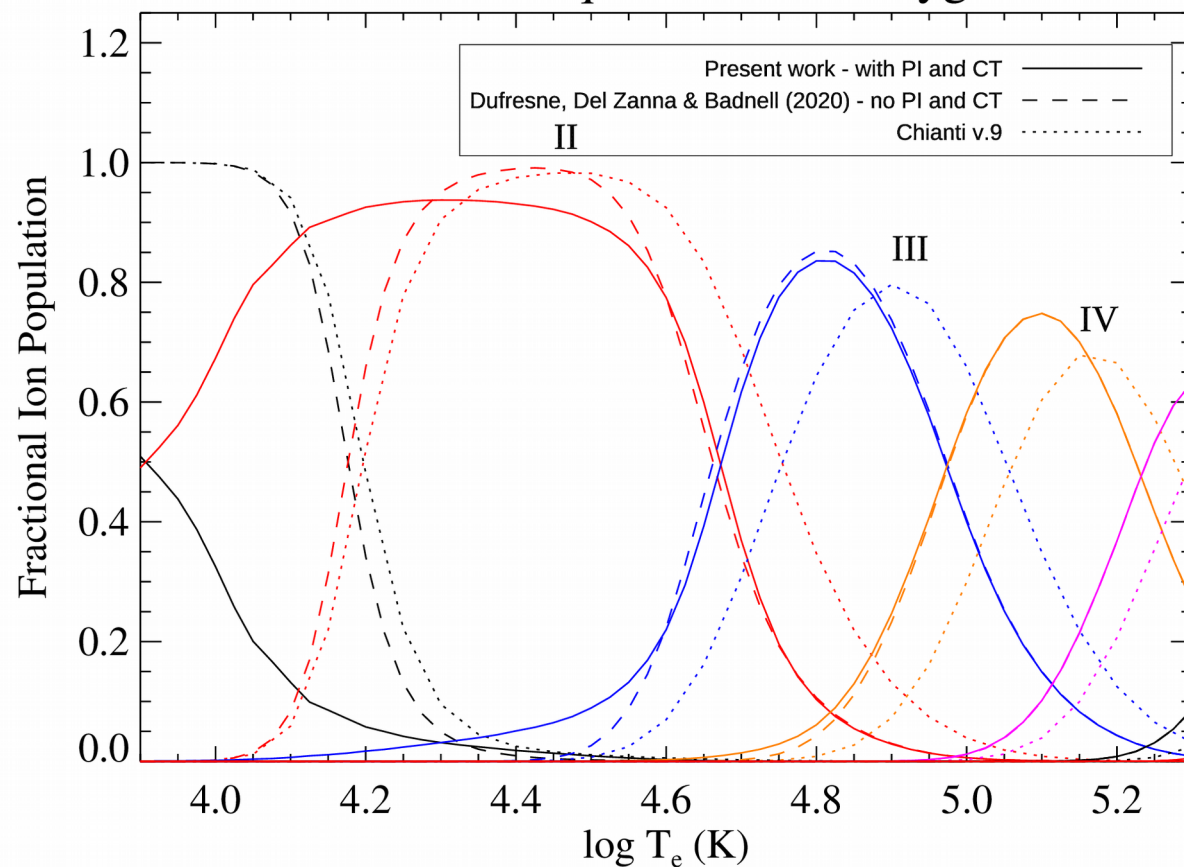
Wang J. G., et al. 2003, Phys. Rev. A, 67, 012710

Wu Y., et al. 2009, Phys. Rev. A, 79, 062711

Results: Ion Populations

With all atomic processes combined

Ionization Equilibrium of Oxygen



- Higher temperature O II lines and O III lines now agree with observations

Comparison with observations

Ion	λ_{obs}	I_{obs}	R_c	R_e	R_f
O II	832.75	11.2 ^a	3.02	2.66	2.20
O II	834.45	35.5 ^a	2.85	2.51	2.08
O II	833.32	24.5 ^a	2.75	2.42	2.01
O II	718.49	15 ^a	2.10	1.39	1.22
O II	796.66	2.84 ^d	1.71	1.32	1.21
O III	1660.80	19.3 ^b	0.44	0.61	0.79
O III	832.92	13.7 ^c	1.21	1.32	1.37
O III	833.74	47.3 ^c	1.06	1.14	1.19
O III	835.10	12.9 ^c	0.98	1.06	1.10
O III	835.26	63.8 ^c	1.09	1.19	1.23
O III	702.89	27.5 ^a	1.16	1.15	1.17

Theoretical to observed intensities

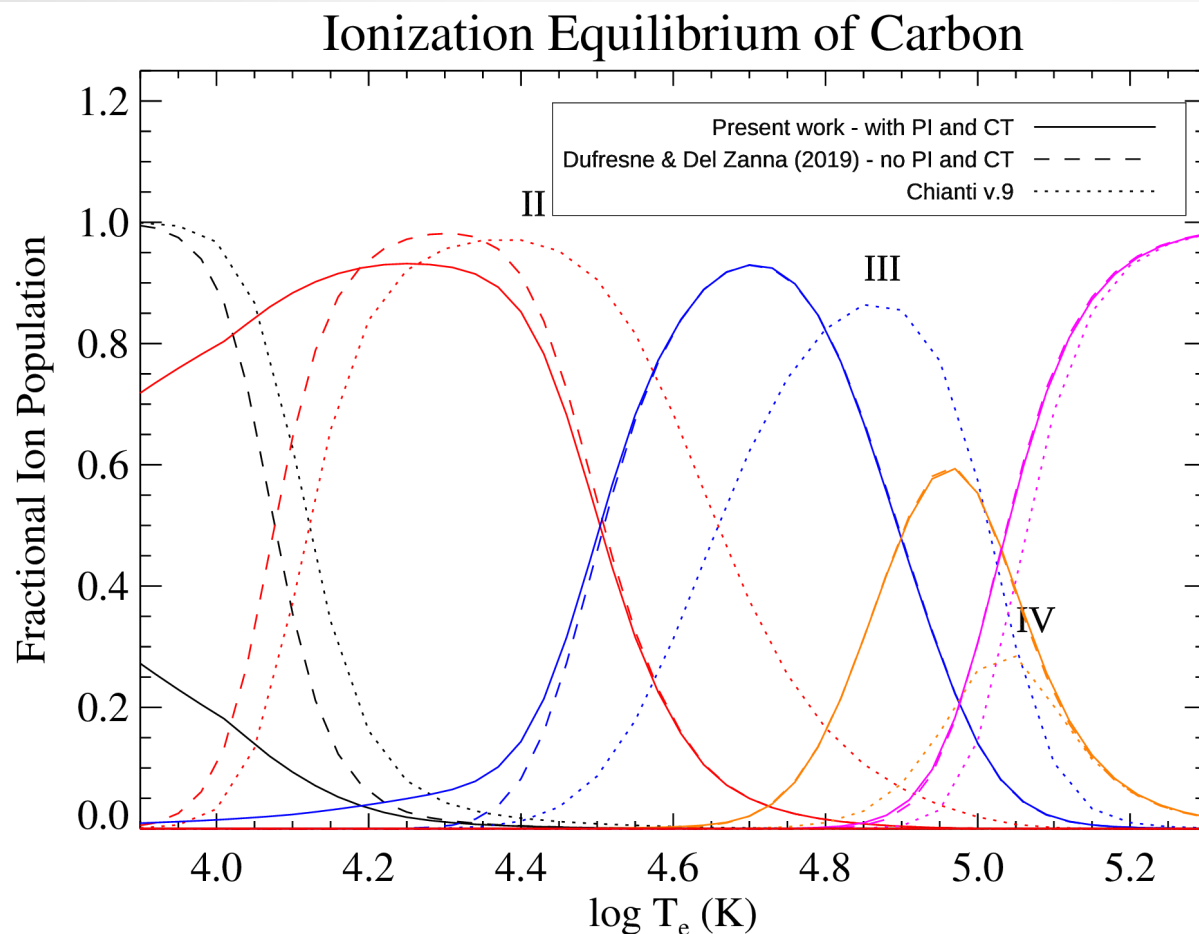
R_c – coronal approximation

R_e – density effects added

R_f – charge transfer and photo-ionisation added

Results: Ion Populations

With all atomic processes combined



Comparison with observations

Ion	λ_{obs}	I_{obs}	R_c	R_e	R_f
C II	1334.53	937 ^a	0.56	0.66	0.94
C II	1335.71	1350 ^a	0.75	0.90	1.29
C II	1036.34	57.9 ^a	0.92	0.81	0.69
C II	1037.00	70.1 ^a	1.50	1.31	1.12
C II	903.99	9.98 ^a	2.22	1.68	1.29
C II	904.46	6.29 ^a	1.78	1.34	1.03
C II	903.59	9.19 ^a	1.62	1.21	0.94
C II	904.14	23.1 ^a	3.21	2.41	1.87
C II	1323.91	1.72 ^b	2.47	1.30	0.98
C III	977.04	702 ^c	0.65	0.86	0.87
C III	1174.88	37.4 ^c	0.65	0.83	0.83
C III	1175.74	104 ^c	0.71	0.89	0.89
C III	1176.37	36.2 ^c	0.67	0.85	0.85
C IV	1548.24	212 ^b	0.43	1.28	1.26
C IV	1550.82	134 ^b	0.34	1.02	1.00

Theoretical to observed intensities

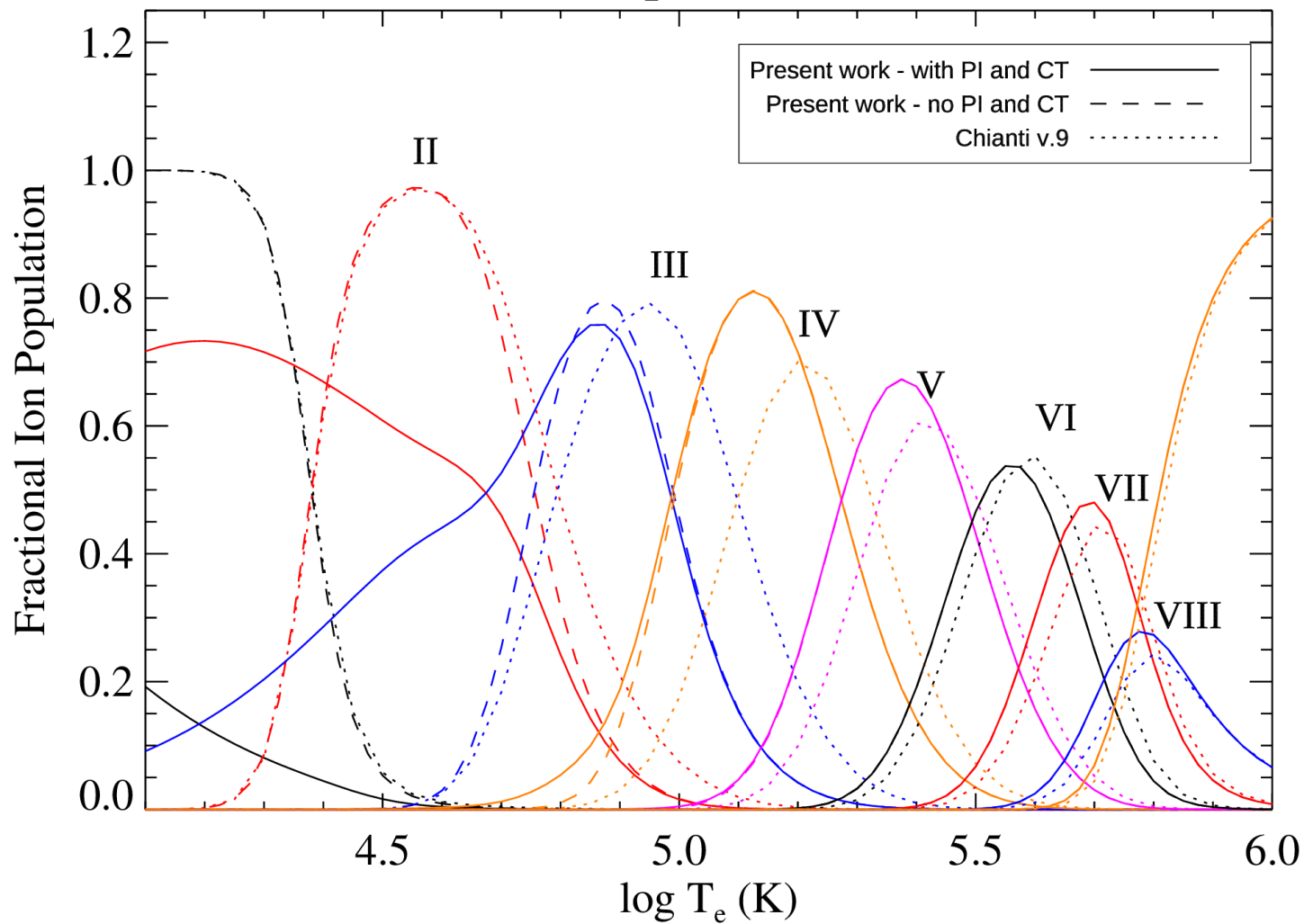
R_c – coronal approximation

R_e – density effects added

R_f – charge transfer and photo-ionisation added

- All predicted intensities in better agreement with observations

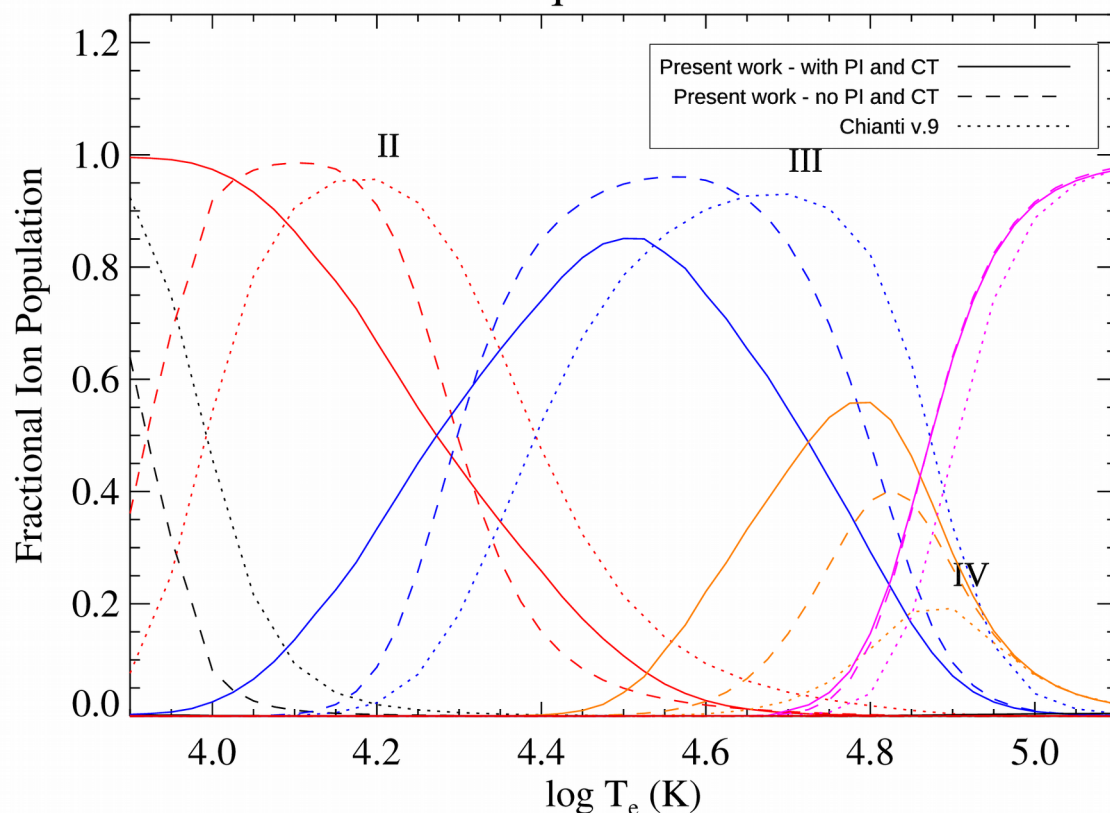
1. **Introduction**
 2. **Background**
 3. **Methodology**
 4. **Results**
 5. **Conclusion**
 6. **References**



Results: Ion Populations

With all atomic processes combined

Ionization Equilibrium of Silicon



Comparison with observations

Ion	λ_{obs}	I_{obs}	R_c	R_e	R_f
Si III	1892.03	832 ^h	0.47	0.85	1.08
Si III	1206.51	630 ^e	0.69	0.87	0.69
Si III	1294.54	4.9 ^e	0.84	0.84	0.60
Si III	1298.89	16.9 ^e	0.83	0.83	0.59
Si III	1296.73	3.8 ^e	0.83	0.84	0.60
Si III	1108.37	4.3 ^e	0.61	0.57	0.40
Si III	1109.97	6.5 ^e	1.00	0.92	0.66
Si III	1113.23	15.5 ^e	1.07	0.97	0.70
Si IV	1393.78	280 ^a	0.06	0.16	0.33
Si IV	1402.77	127 ^a	0.07	0.18	0.37

Theoretical to observed intensities

R_c – coronal approximation

R_e – density effects added

R_f – charge transfer and photo-ionisation added

- Predicted intensities of Si IV resonance lines increase by more than a factor of 5

CT data: Kimura M., et al. 1996, ApJ, 473, 1114

Clarke N., et al. 1999 J.Phys., 31, 533

Wang J. G., et al. 2006, Phys. Rev. A, 74, 052709

Stancil P. C., et al. 1999, J. Phys. B, 32, 1523

Modelling Ion Populations

Summary

- 1) Calculated level-resolved direct and indirect ionization rates
- 2) Metastable levels included in modelling
- 3) Simulated dielectronic recombination suppression in modelling
- 4) Added photo-induced and charge transfer processes
- 5) Improved predicted line intensities compared to observations

Future work

- 1) Find changes in diagnostics from new modelling
- 2) Add simplified optical depth effects for low temperature lines
- 3) Non-Maxwellian electrons
- 4) Time dependent ionisation

Results: Ion Populations

With all atomic processes combined

Ionization Equilibrium of Nitrogen

